## Increased Open-Circuit Voltage and Efficiency in Small Molecule Organic Solar Cells Through the Use of a 56-π Electron Acceptor – Methano Indene Fullerene

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Small molecule organic solar cells (SMOSCs) have made great strides in recent years and efficiencies are now on par with their polymer:fullerene counterparts. However, in all efficient solution processed bulk heterojunction (BHJ) SMOSCs to date the fullerene acceptor has been  $PC_{71}BM$ , which is unfavorable as it has a relatively low lying LUMO that minimizes the open-circuit voltage ( $V_{OC}$ ). ( $V_{OC}$  is proportional to the difference between the HOMO of the donor and LUMO of the acceptor). This approach however has proved far from trivial in the case of polymer:fullerene devices, where a concomitant decrease in the short-circuit current density ( $J_{SC}$ ) is typically observed with most polymer donors blended with high-LUMO fullerene derivatives.  $^{3,4}$ 

Here we demonstrate the application of a high-LUMO 56- $\pi$  fullerene derivative, methano indene fullerene (MIF), in SMOSCs using a dikettopyrrolopyrrole donor (DPP(TBFu)<sub>2</sub>. MIF comprises of asymmetrical adducts where one adduct is indene and the other is dihydromethano and has previously demonstrated high efficiencies with P3HT.<sup>5</sup> DPP(TBFu)<sub>2</sub>:MIF devices are found to have a much improved  $V_{\rm OC}$  (1.03 V) without any significant decrease in the  $J_{\rm SC}$  (9.5 mA/cm<sup>2</sup>), which allows efficiencies of 5.1% to be obtained. In comparison DPP(TBFu)<sub>2</sub>:PC<sub>61</sub>BM devices showed a  $V_{\rm OC}$  of 0.88 V,  $J_{\rm SC}$  = 10.1 mA/cm<sup>2</sup> and an efficiency of 4.5%. Atomic force microscopy and x-ray diffraction studies show that DPP(TBFu)<sub>2</sub>:MIF form a well intermixed BHJ and MIF does not hinder the growth or crystallinity of DPP(TBFu)<sub>2</sub>.

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